



JCT16130IS 130A SCR

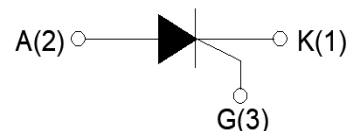
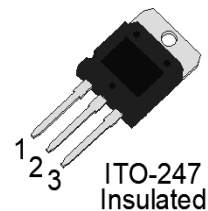
Rev.A.1.2

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT16130IS SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, UPS, SVC, power charger, T-tools etc. From all three terminals to external heatsink, JCT16130IS provides a rated insulation voltage of 2500 V_{RMS} , complying with UL standards (File ref: E252906). Package ITO-247 is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	130	A
V_{DRM}/V_{RRM}	1600	V
I_{GT}	20-80	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range	T_j	-40-125	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	1600	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	1600	V
Average on-state current ($T_c \leq 46^{\circ}C$)	$I_{T(AV)}$	83	A
RMS on-state current ($T_c \leq 46^{\circ}C$)	$I_{T(RMS)}$	130	A
Non repetitive surge peak on-state current ($t_p=10ms$, $T_j=25^{\circ}C$)	I_{TSM}	1500	A
Non repetitive surge peak on-state current ($t_p=8.3ms$, $T_j=25^{\circ}C$)		1650	
I^2t value for fusing ($t_p=10ms$, $T_j=25^{\circ}C$)	I^2t	11250	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=125^{\circ}C$)	dI/dt	250	$A/\mu s$

Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	15	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	25	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG.7)	V_{pp}	1.3	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33\Omega$	20	-	80	mA
V_{GT}		-	-	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ C$ $R_L=3.3k\Omega$	0.25	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	280	mA
I_H	$I_T=1A$	-	-	250	mA
dV/dt	$V_D=1070V$ Gate Open $T_j=125^\circ C$	2000	-	-	V/ μs
t_{on}	$I_G=100mA$ $I_A=1A$ $I_R=100mA$ $T_j=25^\circ C$	-	7	-	μs
t_{off}		-	200	-	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=180A$ $t_p=380\mu s$	$T_j=25^\circ C$	1.6	V
V_{TO}	Threshold voltage	$T_j=125^\circ C$	0.86	V
R_D	Dynamic resistance	$T_j=125^\circ C$	4.5	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ C$	20	μA
I_{RRM}		$T_j=125^\circ C$	12	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	0.4	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (DC)	50	$^\circ C/W$

ORDERING INFORMATION

<u>J</u>	<u>CT</u>	<u>16</u>	<u>130</u>	<u>IS</u>
JieJie Microelectronics Co., Ltd.	SCRs	$16:V_{DRM}/V_{RRM} \geq 1600V$	$I_{T(RMS)}:130A$	IS: ITO-247(Ins)

MARKING

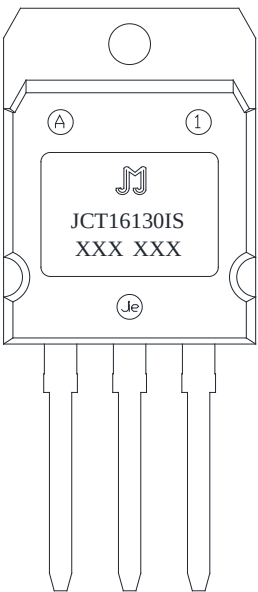
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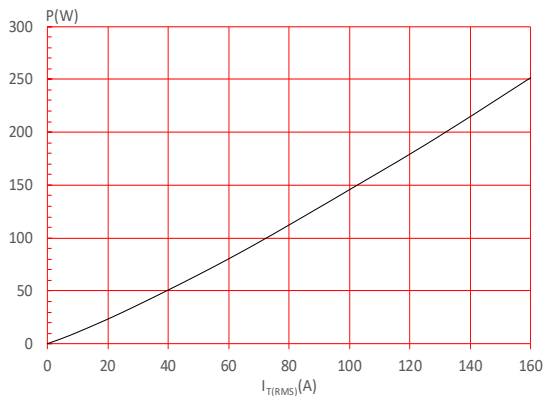
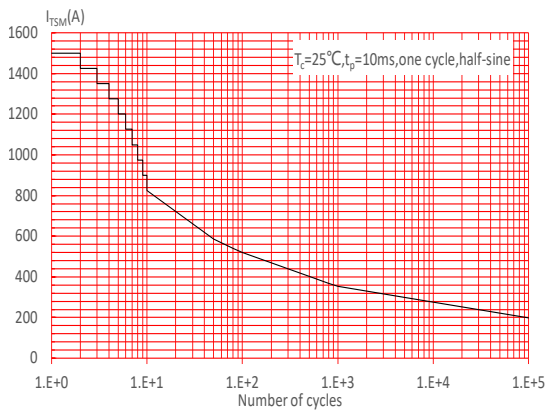
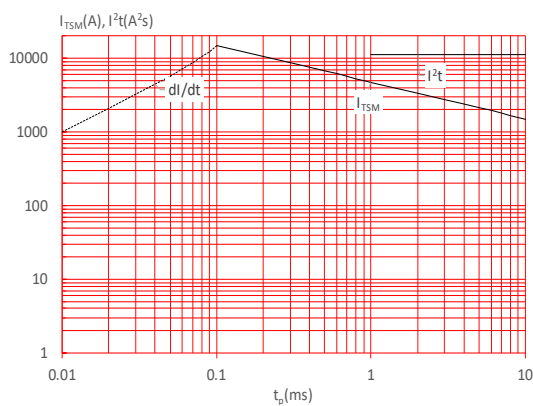
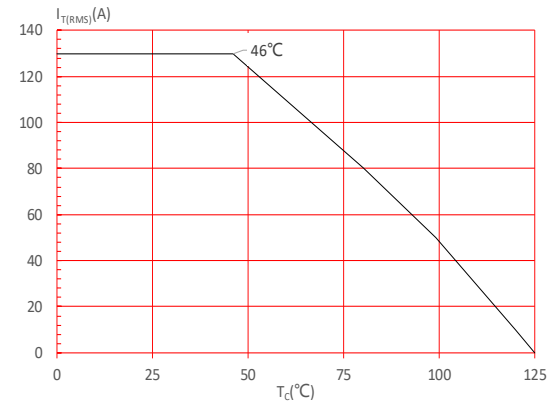
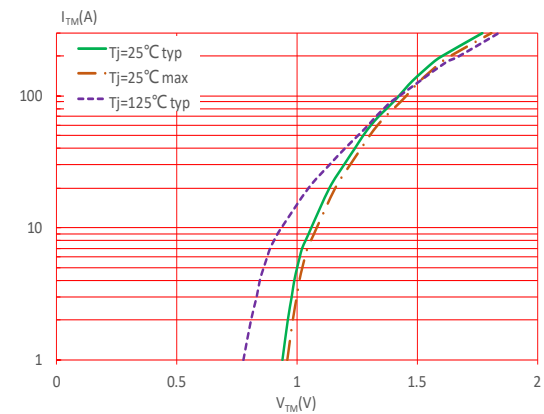
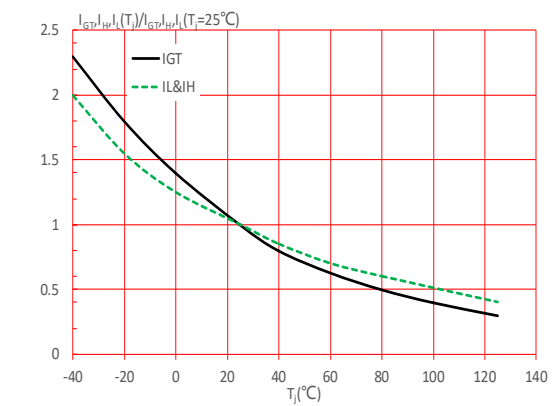
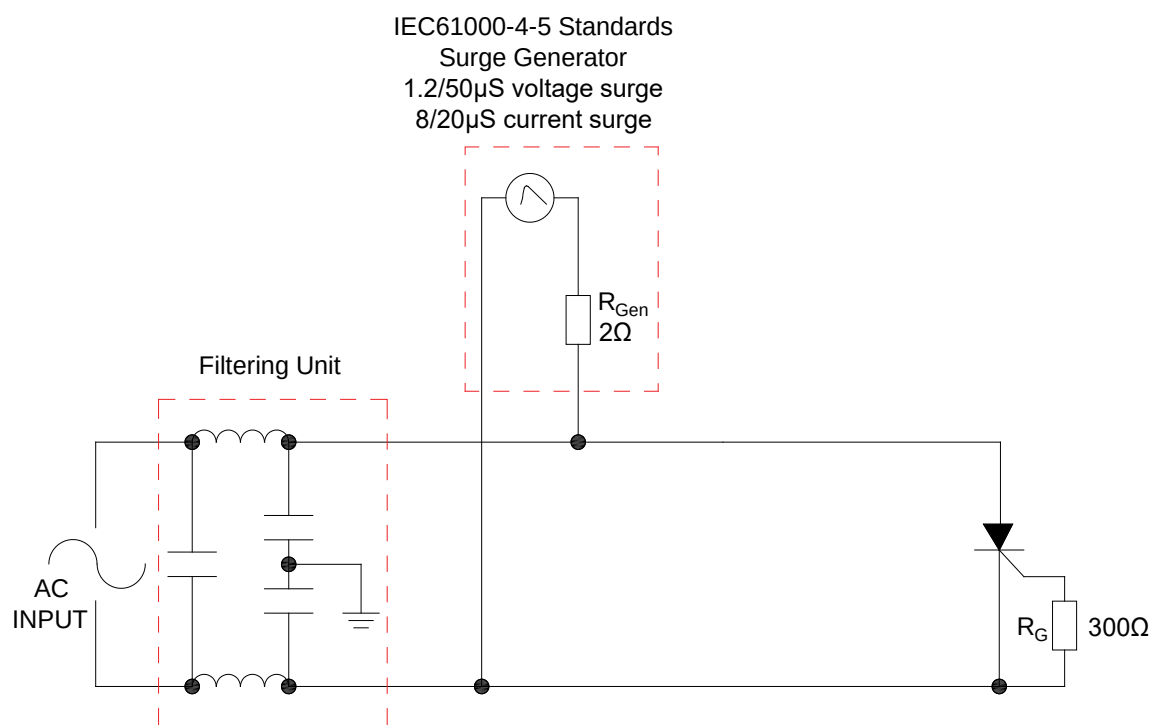
FIG.1: Maximum power dissipation versus RMS on-state current

FIG.3: Surge peak on-state current versus number of cycles

FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 250\text{A}/\mu\text{s}$)

FIG.2: RMS on-state current versus case temperature

FIG.4: On-state characteristics

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



LEAD FORMING AND SOLDERING

Refer to the application note "Assembly Instructions for Thyristors in Through-hole Package" released by JieJie Microelectronics

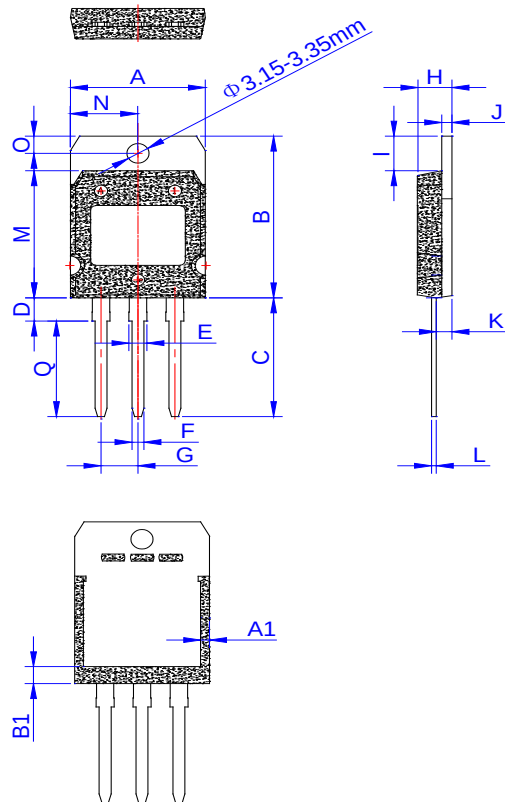
ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT16130IS	1600	20-80	ITO-247(Ins)	25	Tube

Document Revision History

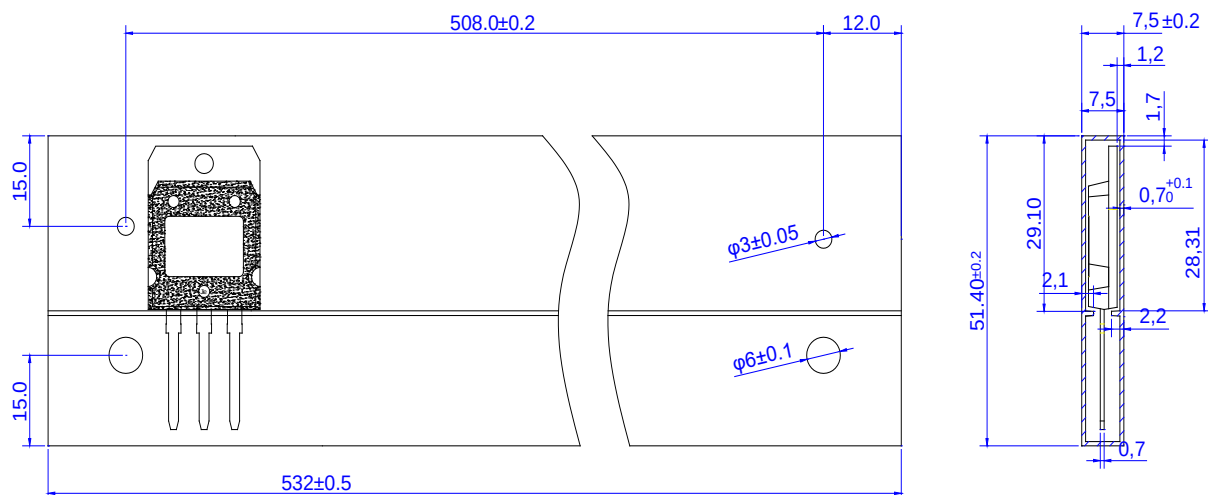
Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update
Feb.19, 2024	A.1.1	Renew $R_{\text{th(j-c)}}$ & V_{TM}
Oct.16, 2025	A.1.2	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	19.70		20.10	0.776		0.791
A1	1.10		1.50	0.043		0.059
B	26.90		27.30	1.059		1.075
B1	2.65		3.05	0.104		0.120
C	19.40		20.40	0.764		0.803
D	3.80		4.00	0.150		0.157
E	2.56		2.76	0.101		0.109
F	1.66		1.86	0.065		0.073
G	5.25		5.65	0.207		0.222
H	5.05		5.50	0.199		0.217
I	5.60		6.00	0.220		0.236
J	1.45		1.55	0.057		0.061
K	2.20		2.40	0.087		0.094
L	0.60		0.80	0.024		0.031
M	21.20		21.40	0.835		0.843
N	9.70		10.30	0.382		0.406
O	2.60		3.20	0.102		0.126
Q	15.80		16.20	0.622		0.638

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
ITO-247	TUBE	25	400	1,600

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